

Fig. 1

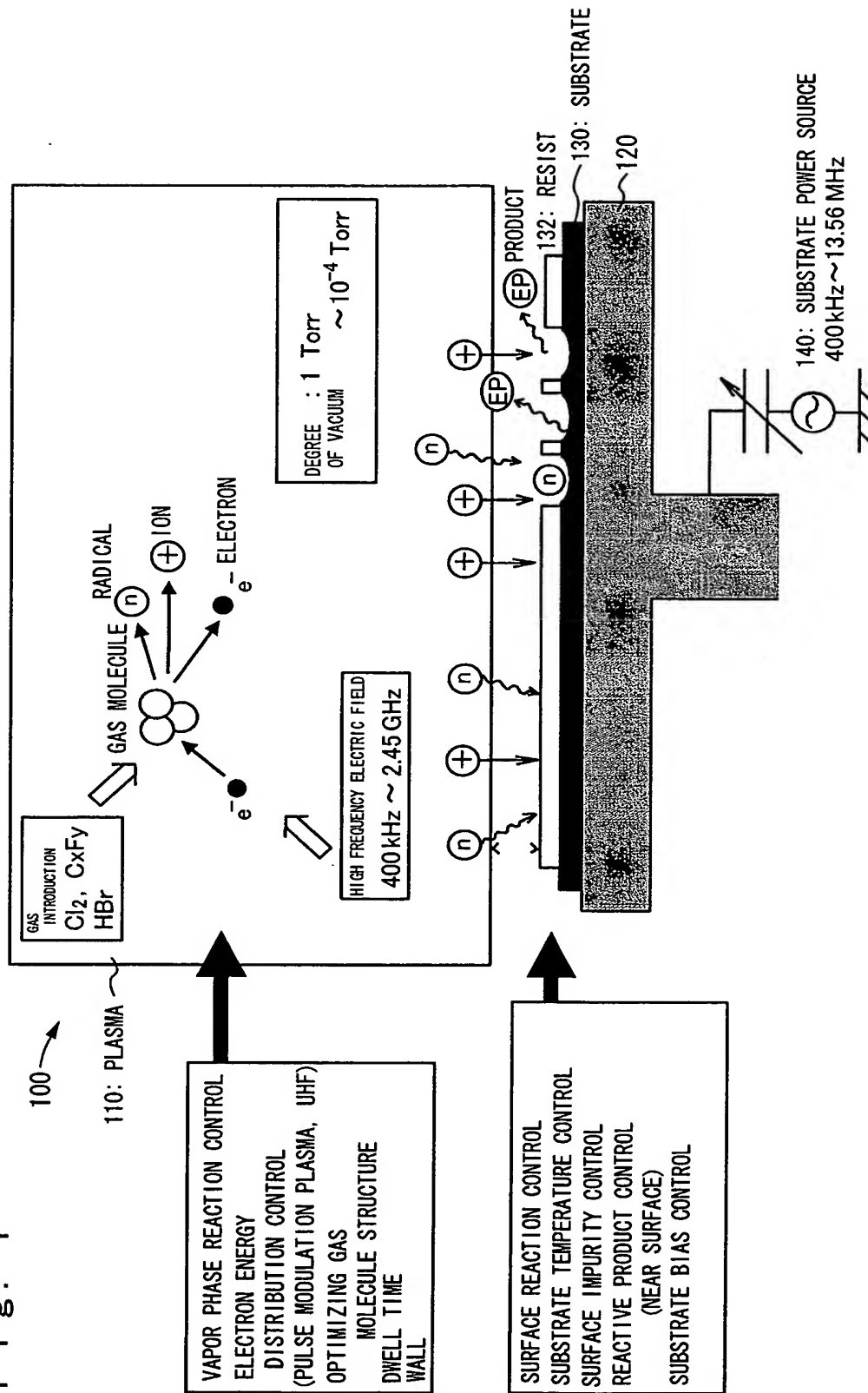


Fig. 2

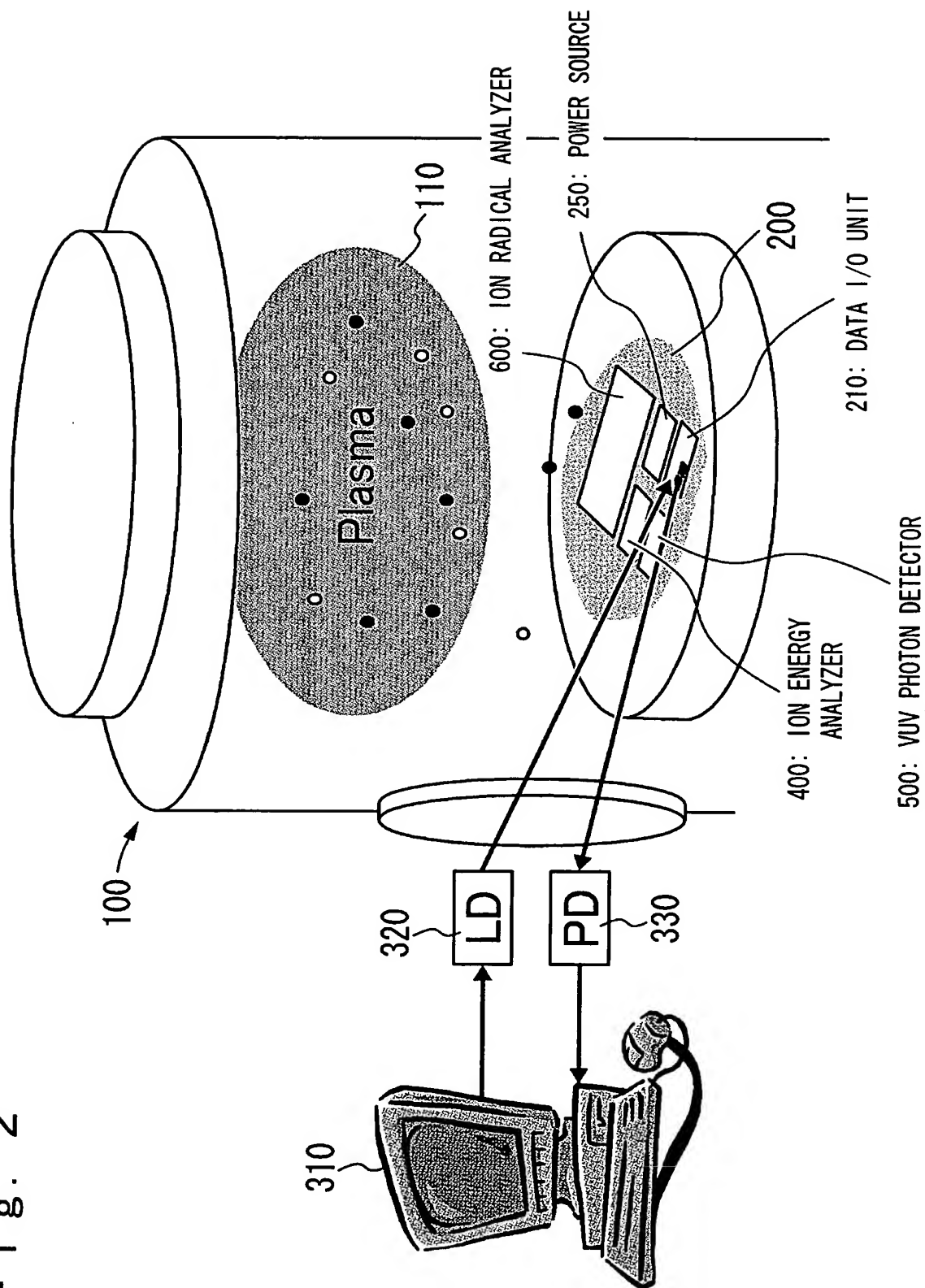


Fig. 3

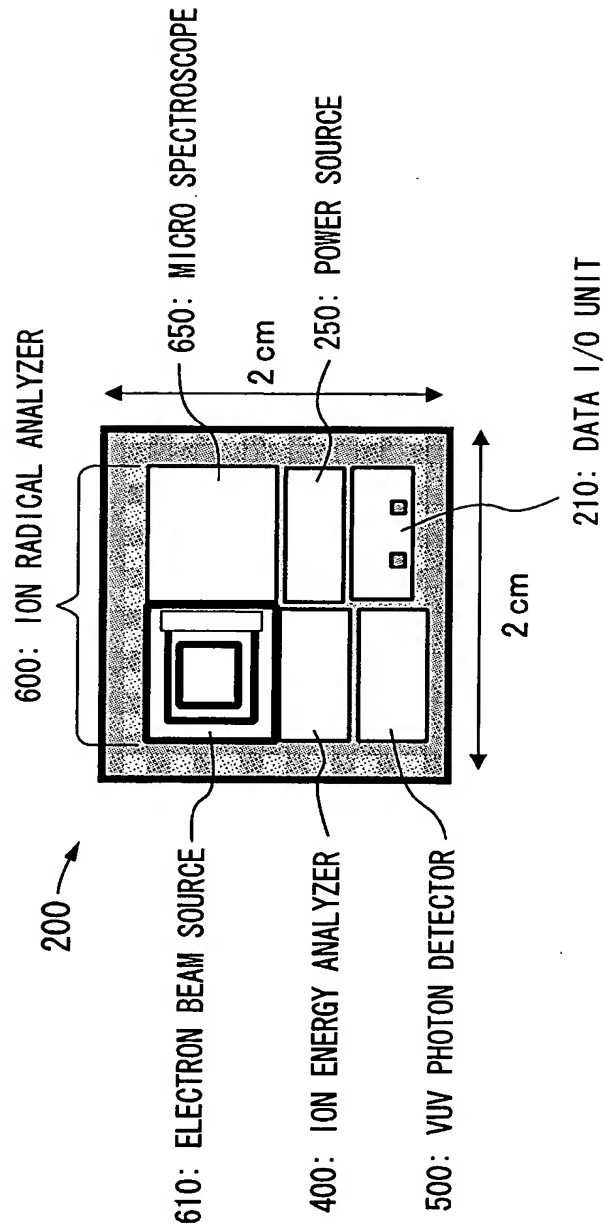


Fig. 5

POTENTIAL DIFFERENCE BETWEEN PLASMA SPACE POTENTIAL
AND GROUND IS UTILIZED.

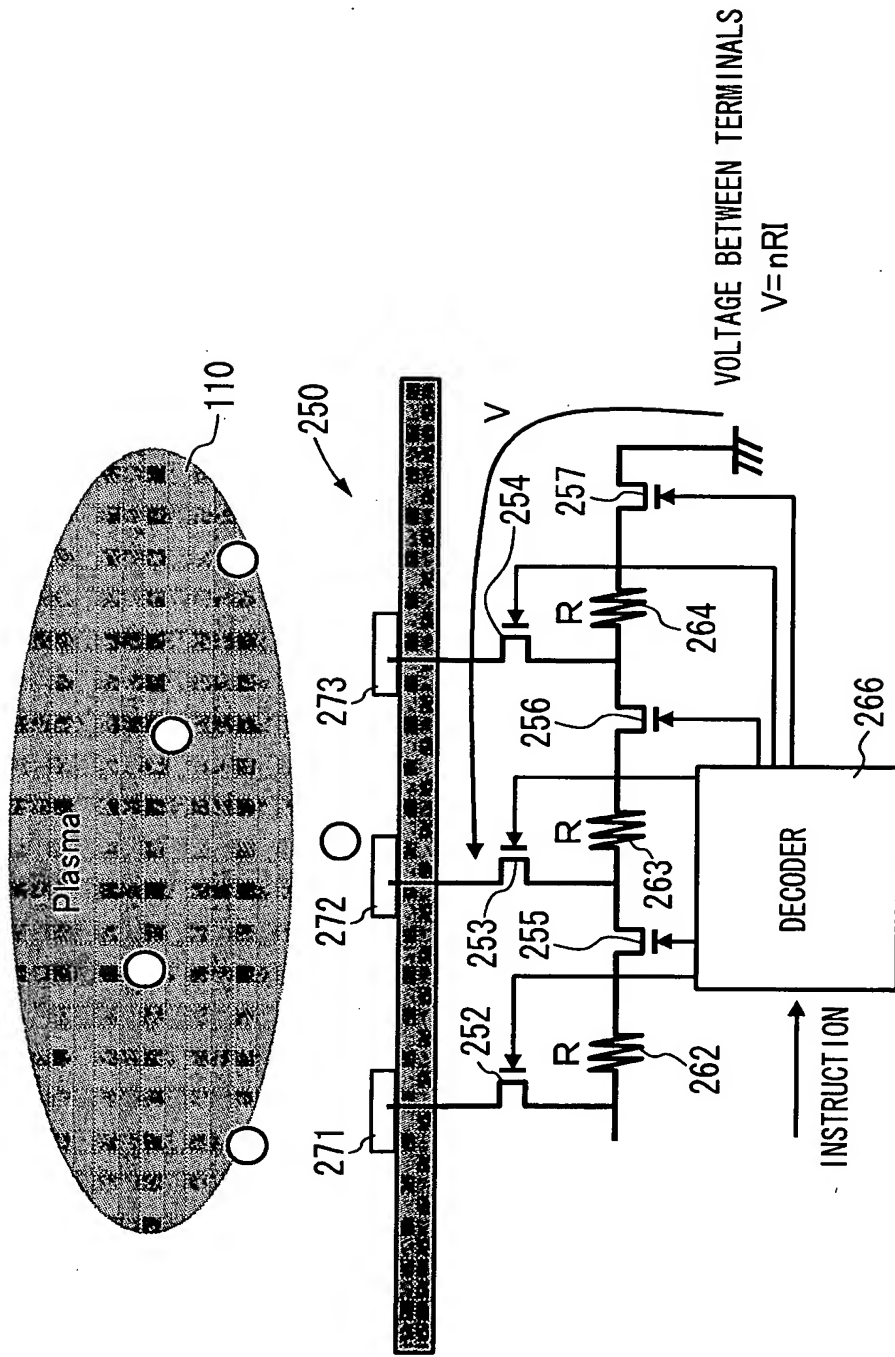
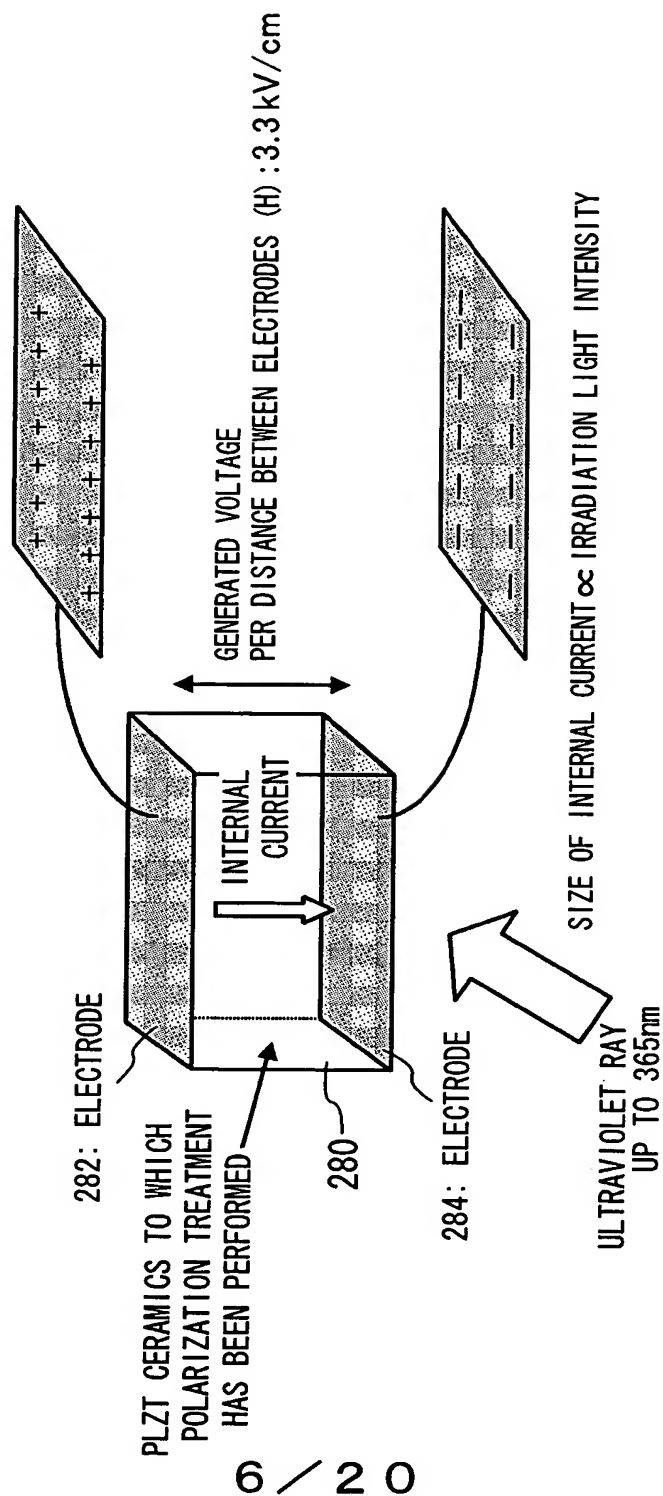


Fig. 6



F i g . 7

STRUCTURE OF ON-WAFER ION ENERGY ANALYZER

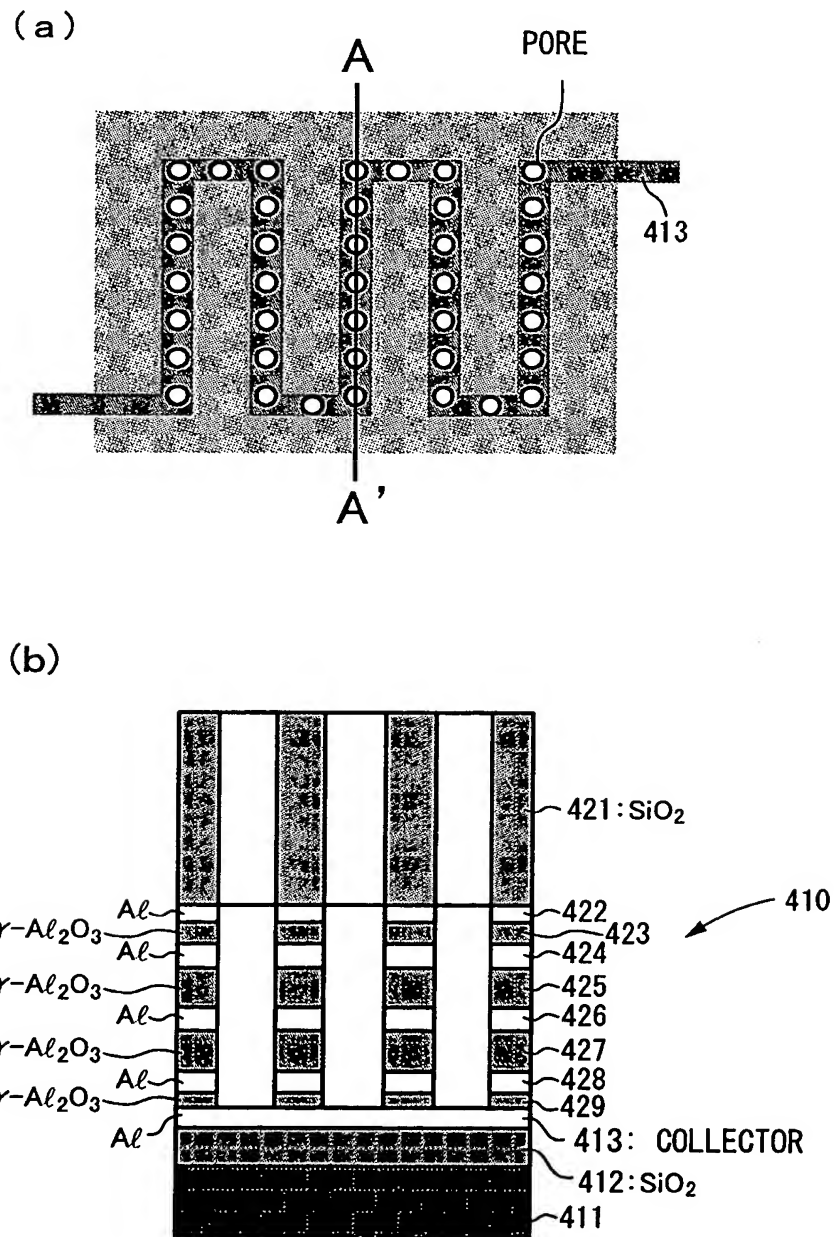
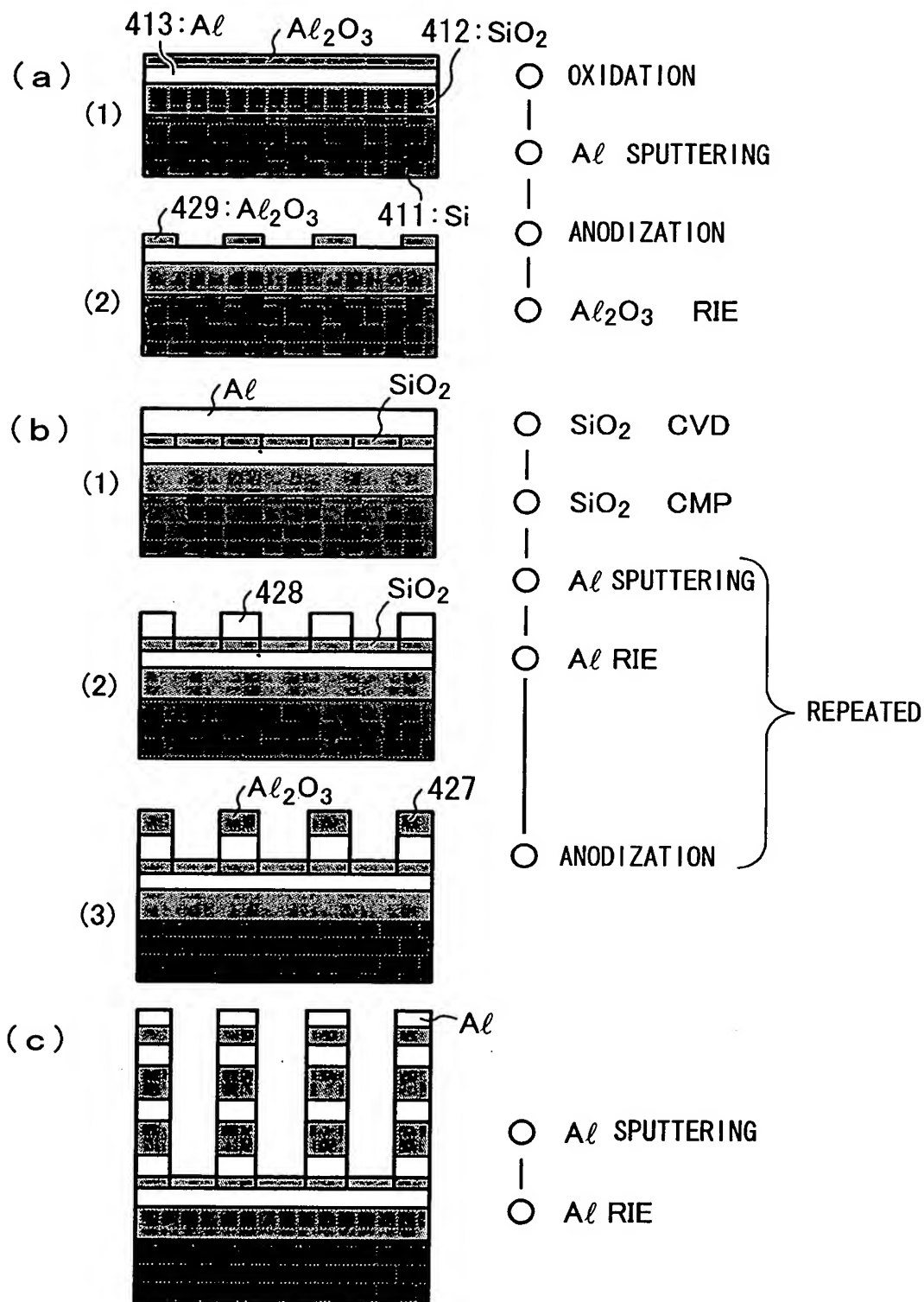


Fig. 9



F i g. 10

(d)

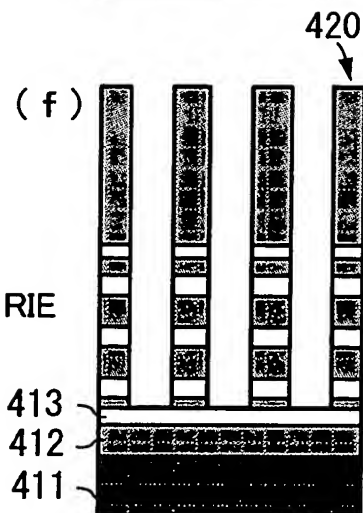
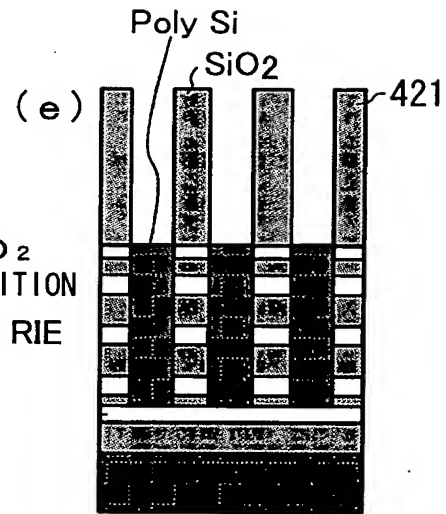
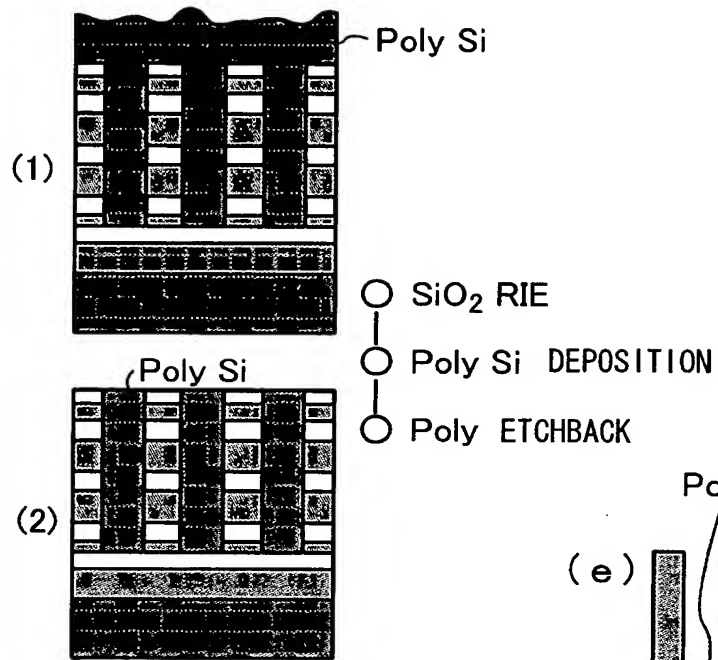


Fig. 11

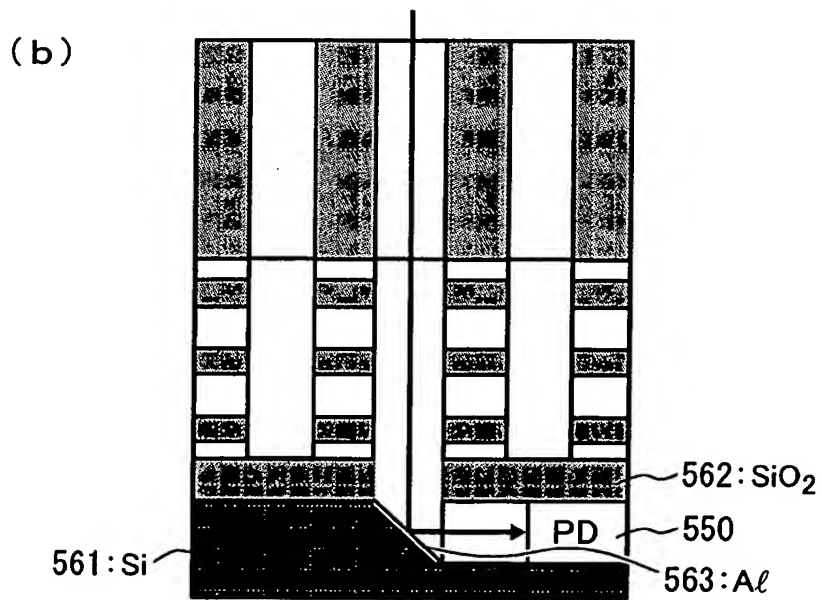
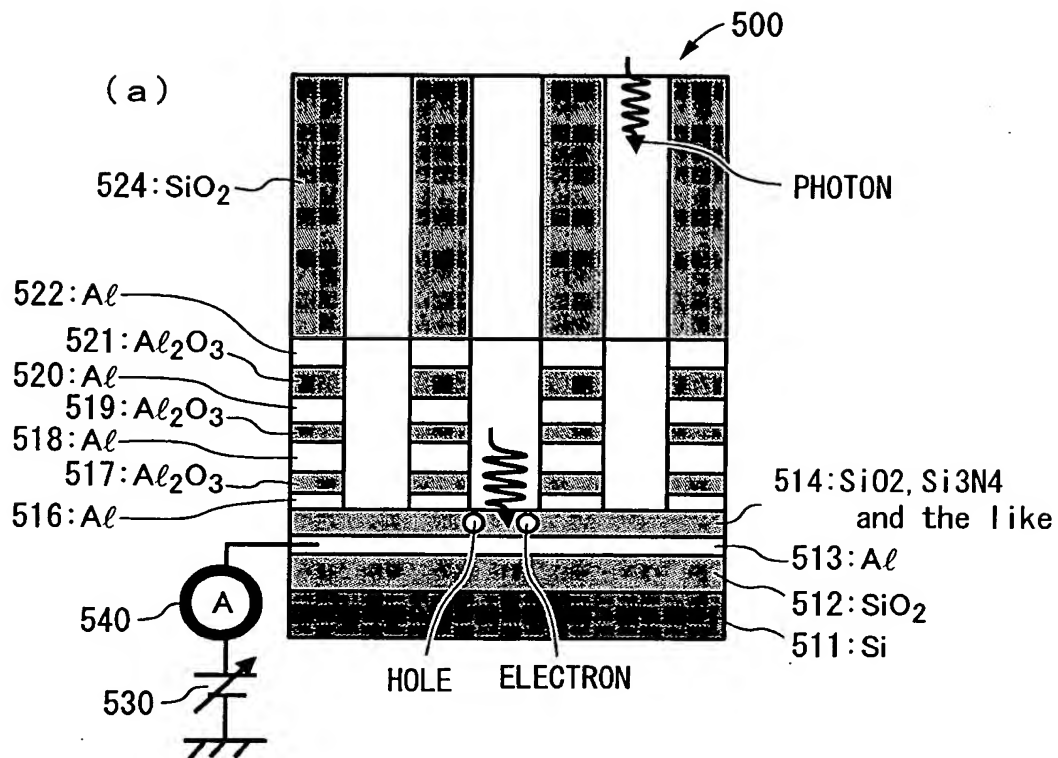


Fig. 12

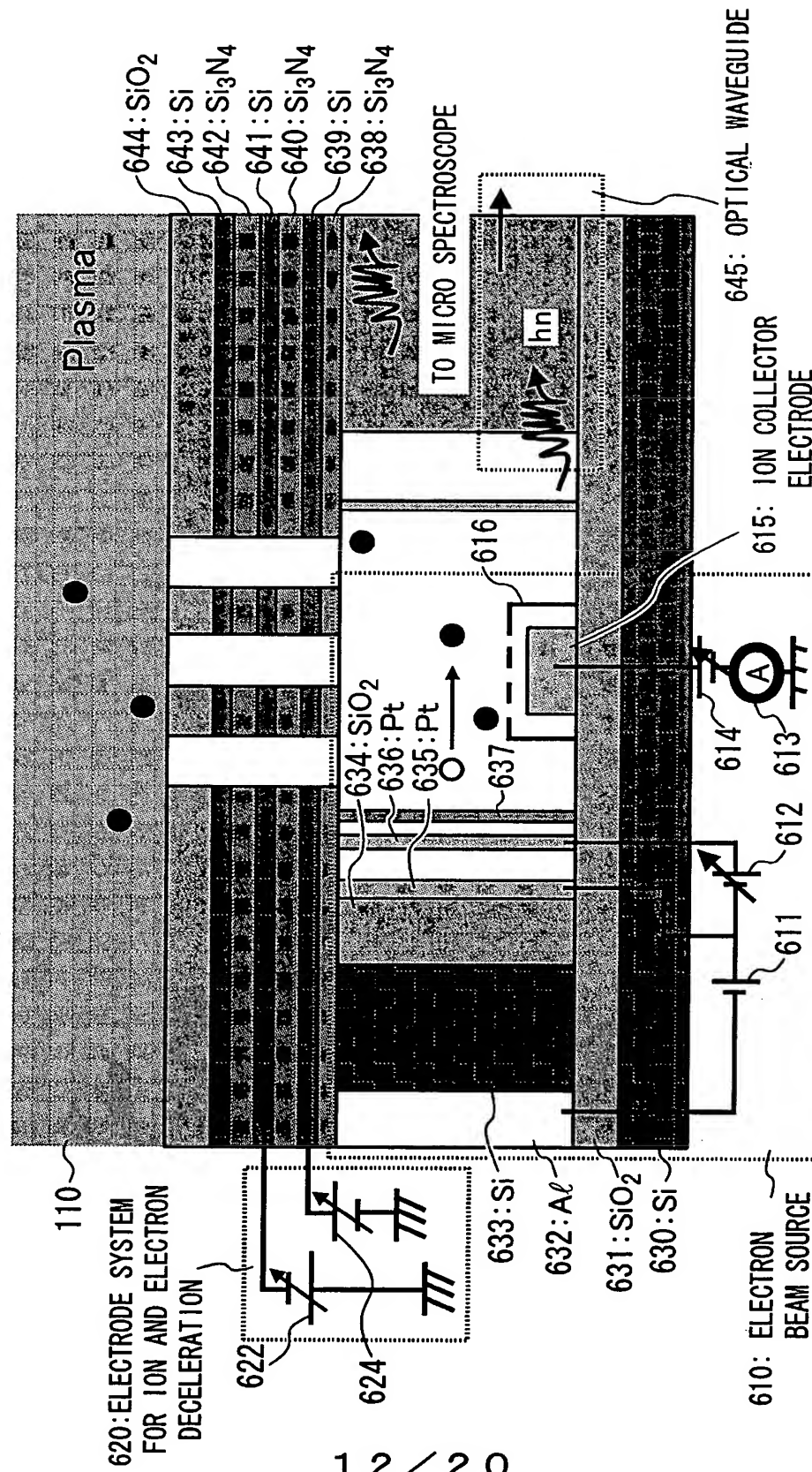


Fig. 13

FIELD EMISSION TYPE ELECTRON GUN

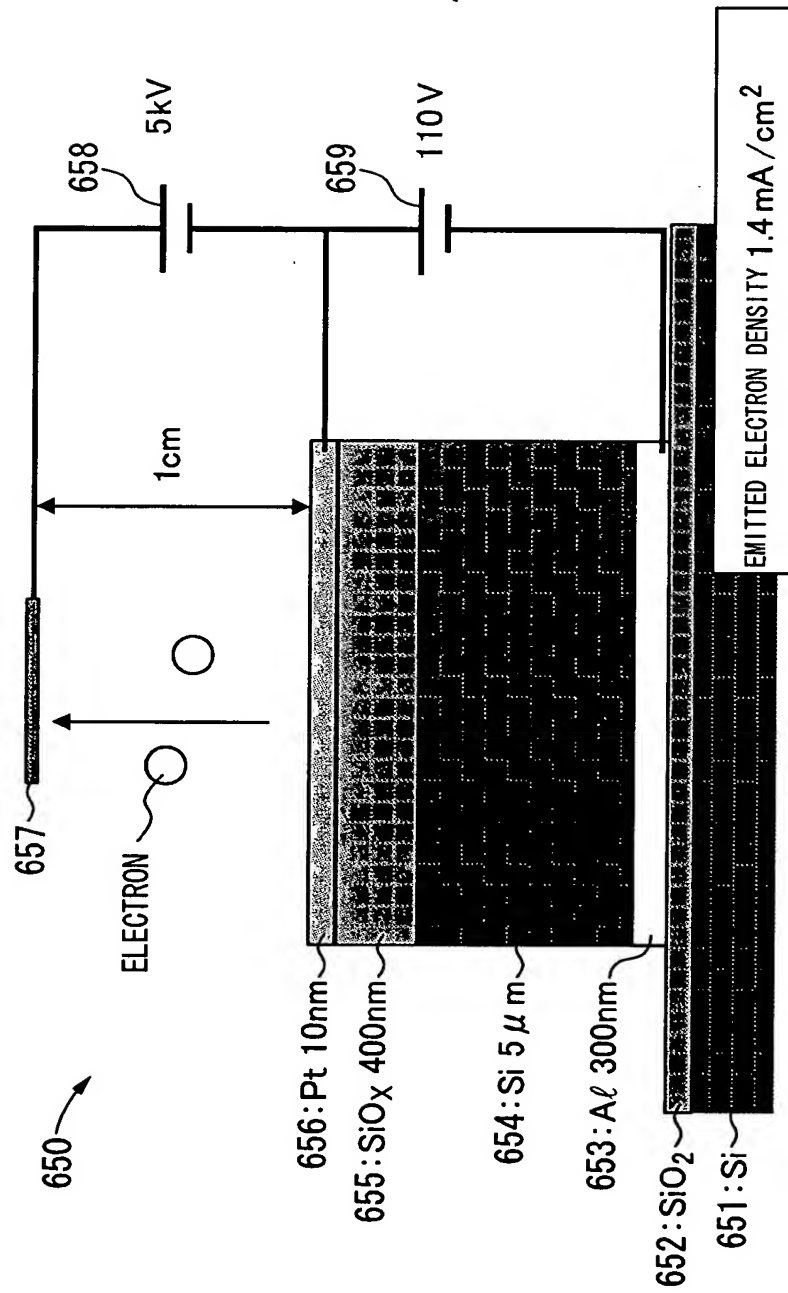


Fig. 14

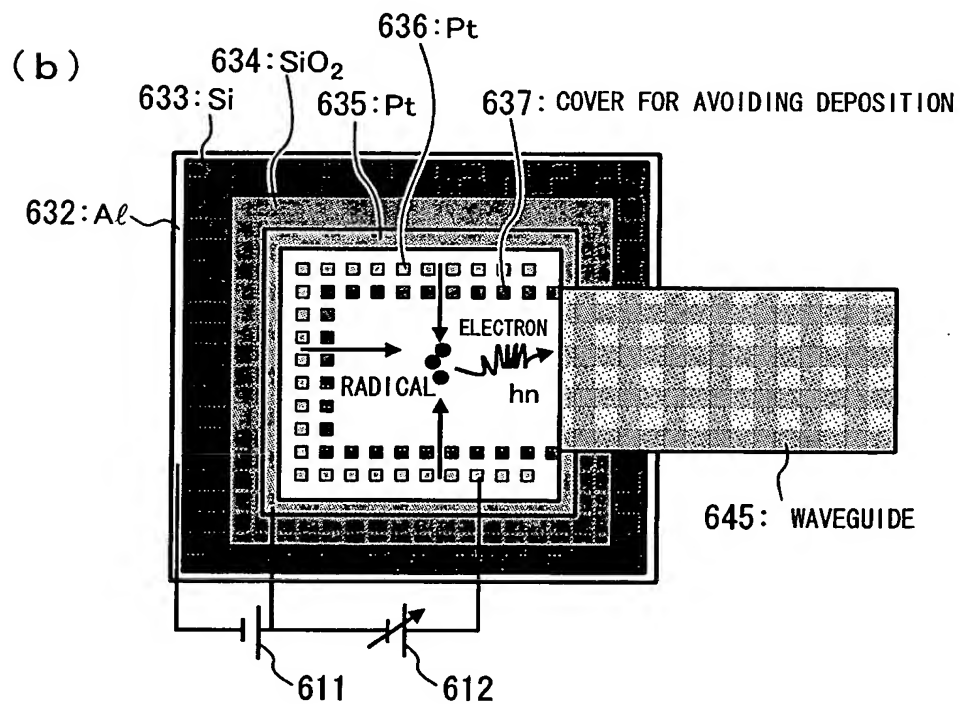
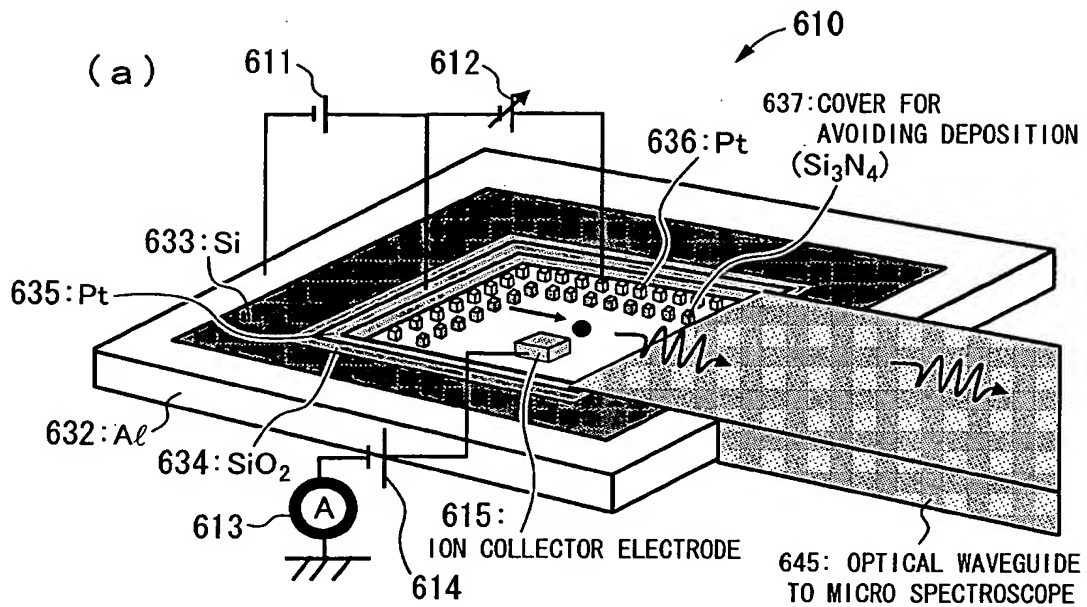


Fig. 15

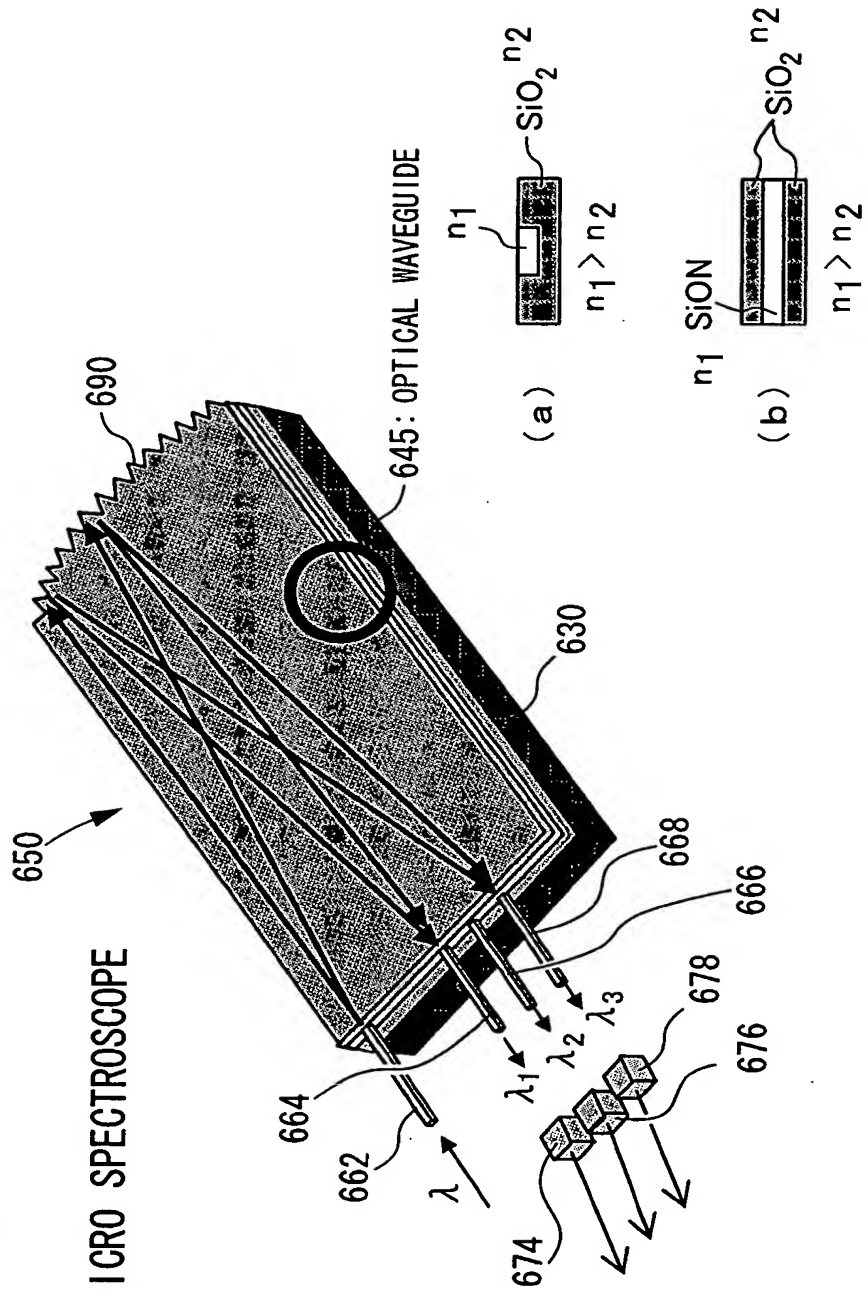


Fig. 16

MANUFACTURING PROCESS OF MICRO ION RADICAL ANALYZER(1)

(a) OXIDATION



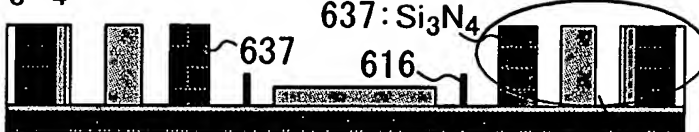
(b) Si DEPOSITION, ETCHING



(c) Al VAPOR DEPOSITION, ETCHING

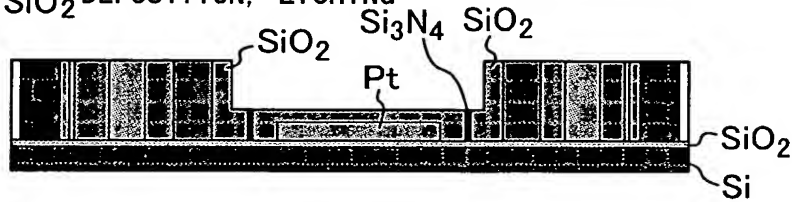
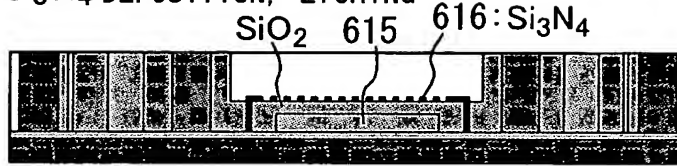
(d) SiO_2 DEPOSITION, ETCHING

(e) Pt DEPOSITION, PATTERNING

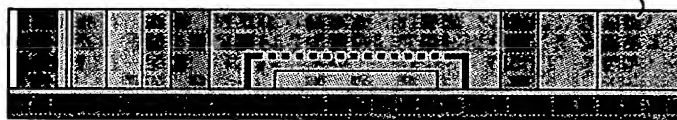
(f) Si_3N_4 DEPOSITION, ETCHING

F i g. 17

MANUFACTURING PROCESS OF MICRO ION RADICAL ANALYZER (2)

(g) SiO_2 DEPOSITION, ETCHING(h) Si_3N_4 DEPOSITION, ETCHING(i) SiO_2 DEPOSITION, ETCHING
FORMATION OF WAVEGUIDE

645: ION DOPING

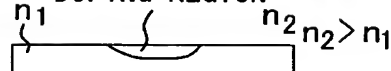
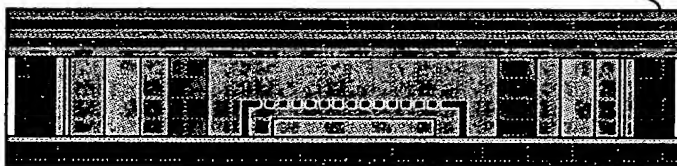


ELECTRON BEAM SOURCE



WAVEGUIDE

DOPING REGION

(j) Si_3N_4 , Si DEPOSITION643: Si_3N_4 

642: Si
641: Si_3N_4
640: Si
649: Si_3N_4

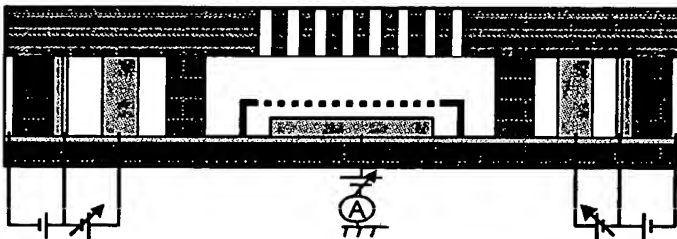
(k) Si_3N_4 , Si ETCHING
 SiO_2 SACRIFICE LAYER ETCHING13.2 μm

Fig. 18

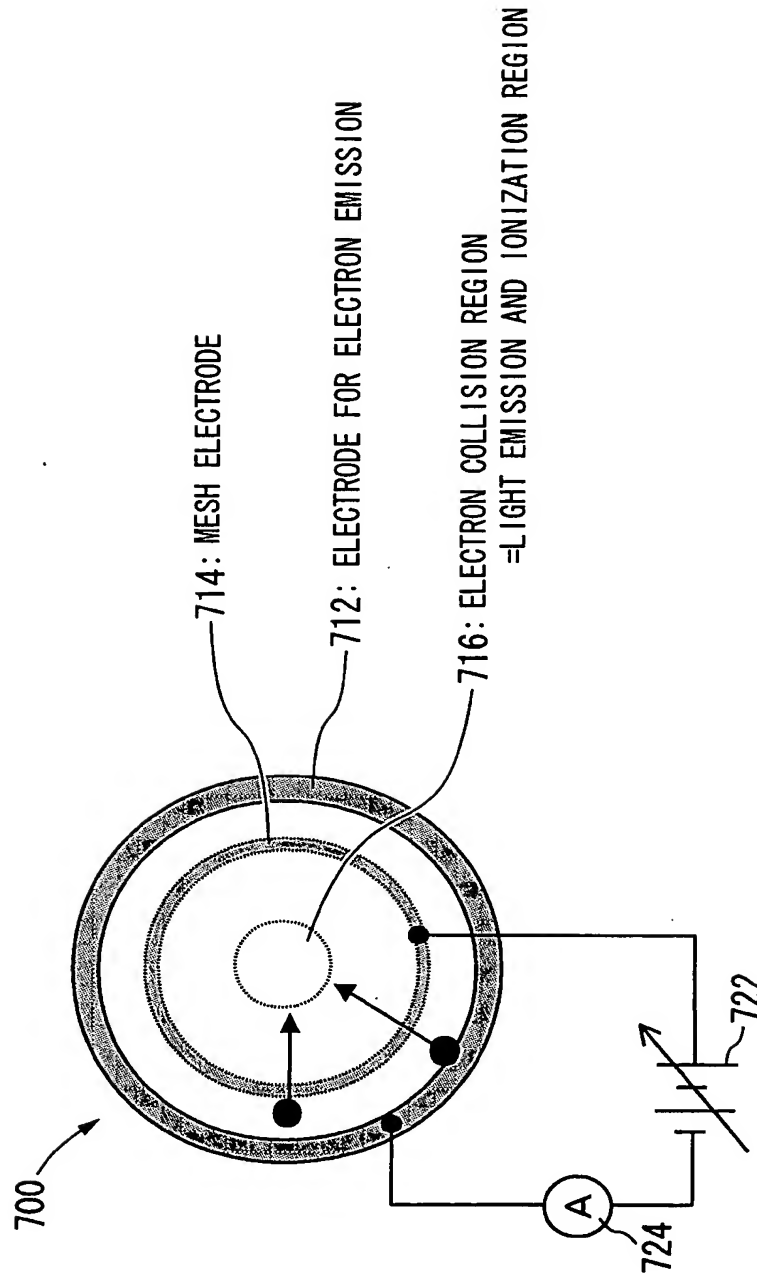


Fig. 19

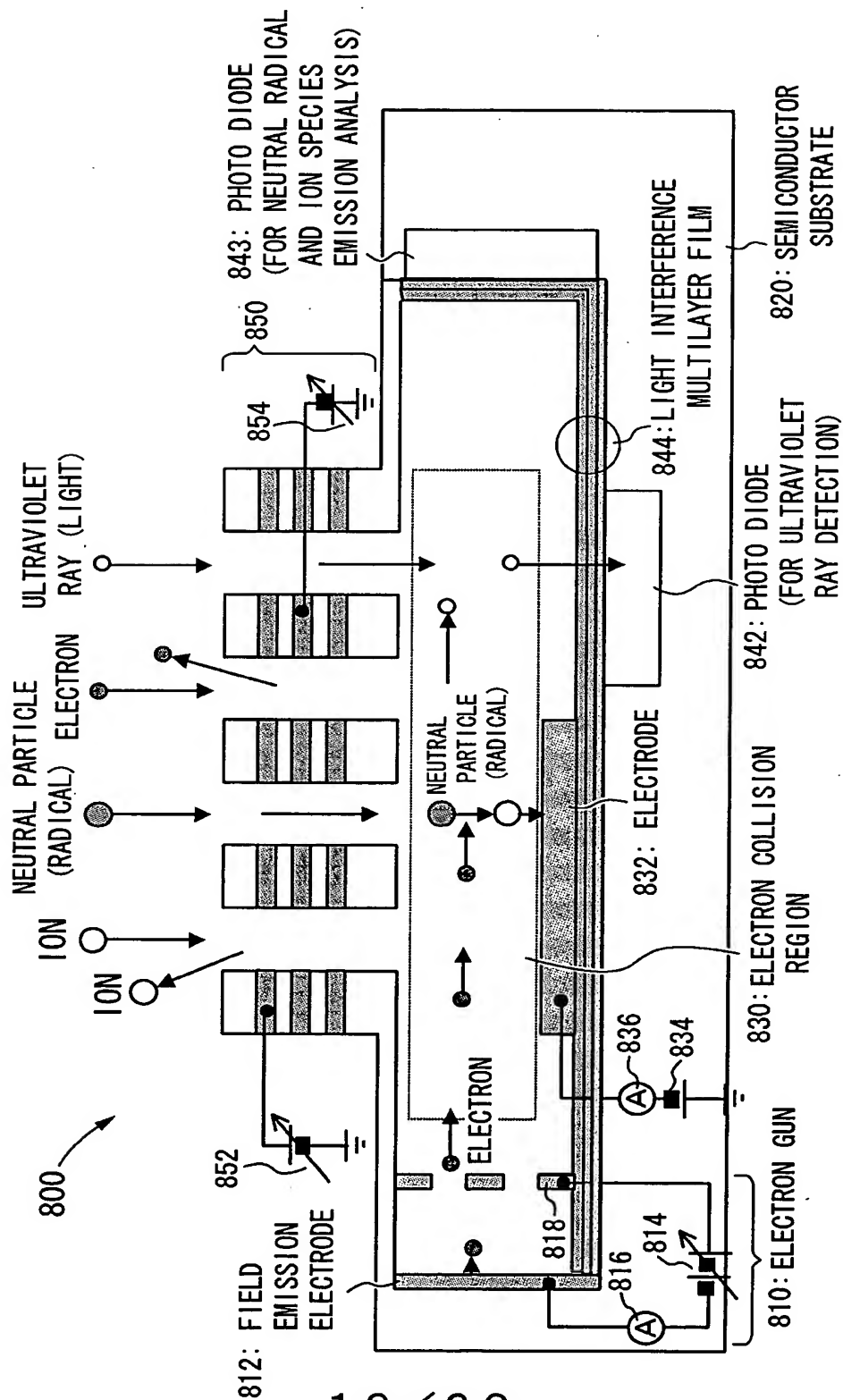


Fig. 20

